What is claimed is:

1. A fabrication method for a semiconductor CSP type package, comprising the steps of:

cutting a wafer on which LSI chips are formed to separate said LSI chips;

providing gaps around said LSI chips at equal intervals to array said LSI chips; and

burying said gaps with an LSI chips insulative resin to enlarge a wire forming area, thereby providing an external-terminal mounting area extending farther outward from a peripheral edge of each of said LSI chips.

2. The fabrication method according to claim 1, wherein each of said LSI chips has an alignment mark for photolithography and said alignment mark is used to align patterning on said each LSI chip in said step of forming said wire forming area and said external-terminal mounting area.

3. The fabrication method according to claim 1, wherein said LSI chips are only those chips which have been screened as good after separation.

4. The fabrication method according to claim 2, wherein said LSI chips are only those chips which have been screened as good after separation.

5. The fabrication method according to claim 1, wherein said LSI chips are adhered to a substrate with said gaps provided.

6. The fabrication method according to claim 2, wherein said LSI chips are adhered to a substrate with said

gaps provided.

7. The fabrication method according to claim 1, wherein said gaps are provided by adhering said wafer to an stretchable sheet, then cutting said wafer to separate said LSI chips and stretching said sheet isotropically.

8. The fabrication method according to claim 2, wherein said gaps are provided by adhering said wafer to an stretchable sheet, then cutting said wafer to separate said LSI chips and stretching said sheet isotropically.